

Attorney's Docket No.: 57017.P025

Patent

In re the Application of: Chen, J. et al.

(inventor(s))

Serial No.: 07863.791

Filed: April 6, 1992

AMENDMENT UNDER
37 C.F.R. § 1.116
EXPEDITED PROCEDURE
EXAMINING GROUP 2503

For: METHOD FOR IMPROVED LITHOGRAPHIC PATTERNING IN A SEMICONDUCTOR FABRICATION PROCESS
(title)

THE COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231
Box AF

SIR: Transmitted herewith is an **Amendment After Final Action** for the above application.

- ☐ Small entity status of this application under 37 C.F.R. §§ 1.9 and 1.27 has been established by a verified statement previously submitted.
- ☐ A verified statement to establish small entity status under 37 C.F.R. §§ 1.9 and 1.27 is enclosed.
- ☒ No additional fee is required.
- ☐ A Notice of Appeal is enclosed.

The fee has been calculated as shown below:

| (Col. 1) | | (Col. 2) | | (Col. 3) | SMALL ENTITY | | OTHER THAN A SMALL ENTITY | |
|--|-----------------------------|----------|---------------------------------|---------------|--------------|----------------|---------------------------|----------------|
| | Claims Remaining After Amd. | | Highest No. Previously Paid For | Present Extra | Rate | Additional Fee | Rate | Additional Fee |
| Total Claims | * | Minus | ** | 0 | x11 | \$ | x22 | \$ -0- |
| Indep. Claims | * | Minus | *** | 0 | x37 | \$ | x74 | \$ -0- |
| <input type="checkbox"/> First Presentation of Multiple Dependent Claim(s) | | | | | +115 | \$ | +230 | \$ -0- |
| | | | | | Total | | Total | |
| | | | | | Add. Fee | \$ | Add. Fee | \$ -0- |

* If the entry in Col. 1 is less than the entry in Col. 2, write "0" in Col. 3.

** If the "Highest No. Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.

*** If the "Highest No. Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space.
The "Highest No. Previously Paid For" (Total or Independent) is the highest number found from the equivalent box in Col. 1 of a prior amendment or the number of claims originally filed.

- ☐ A check in the amount of \$_____ is attached for presentation of additional claim(s).
- ☐ Applicant(s) hereby Petition(s) for an Extension of Time of _____ month(s) pursuant to 37 C.F.R. § 1.136(a).
- ☐ A check for \$_____ is attached for processing fees under 37 C.F.R. § 1.17.
- ☐ Please charge my Deposit Account No. 02-2666 the amount of \$_____.
- ☐ A duplicate copy of this sheet is enclosed.
- ☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 02-2666 (a duplicate copy of this sheet is enclosed):
- ☒ Any additional filing fees required under 37 C.F.R. § 1.16 for presentation of extra claims.
- ☒ Any extension or petition fees under 37 C.F.R. § 1.17.

BLAKELY SOKOLOFF TAYLOR & ZAFMAN

Bradley J. Berezna

Reg. No. 33474

Date: September 9, 1993

12400 Wilshire Boulevard
Seventh Floor
Los Angeles, California 90025
(408) 720-8598

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, D.C. 20231

on September 9, 1993
Date of Deposit

Pearl E. Dworkin
Name of Person Mailing Correspondence

Signature

Date

(LJV/cak 11/23/92)

57017-P025

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

CHEN, J. et al.

Serial No.: 07/863,791

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SEMICONDUCTOR FABRICATION
PROCESS

Examiner: Dodson, S.

Art Unit: 1503

Patent

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GROUP 1500

Amendment To Final Office Action

Box AF
Hon. Commissioner of
Patents and Trademarks
Washington, D.C. 20231

Sirs:

In response to the Office Action mailed August 6, 1993, please consider the following amendment and consider the following remarks.

IN THE CLAIMS:

1. (Twice Amended) A method of lithographically printing a two-dimensional feature on a substrate, said feature having first and second edges spaced in close proximity to one another, said method comprising the steps of:

- (a) depositing a radiation-sensitive material on said substrate;
- (b) providing a first mask image segment which corresponds to said first edge;
- (c) exposing said first mask image segment with radiation using an imaging tool to produce a first pattern edge gradient, said first pattern edge gradient defining said first edge of said two-dimensional feature in said material;
- (d) providing a second mask image segment which corresponds to said second edge;